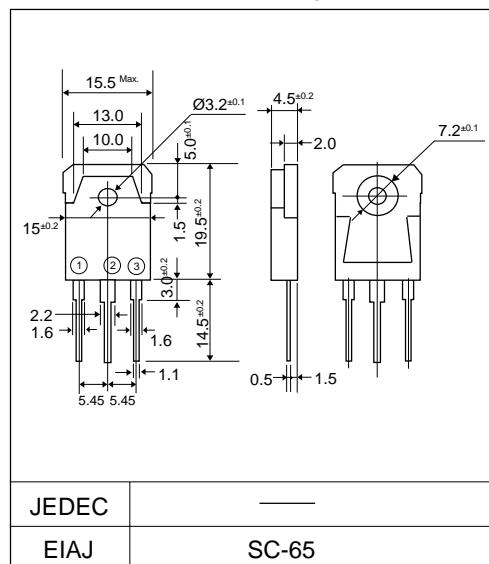


SCHOTTKY BARRIER DIODE

■ Outline drawings, mm



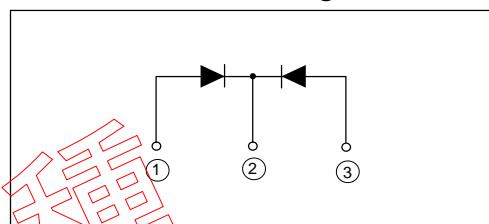
■ Features

- Low VF
- Super high speed switching
- High reliability by planer design

■ Applications

- High speed power switching

■ Connection diagram



■ Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak reverse voltage	V _{RRM}		60	V
Non-repetitive peak reverse voltage	V _{RSM}	t _w =500ns, duty=1/40	60	V
Average output current	I _O	Square wave, duty=1/2 T _c =113°C	60*	A
Surge current	I _{FSM}	Sine wave 10ms	500	A
Operating junction temperature	T _j		-40 to +150	°C
Storage temperature	T _{stg}		-40 to +150	°C

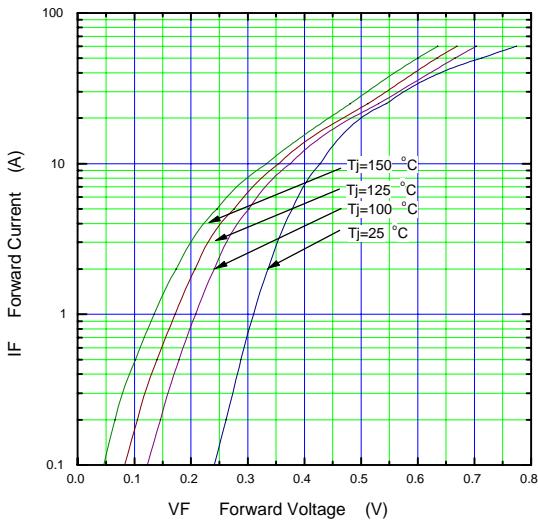
* Average forward current of centertap full wave connection

- Electrical characteristics (Ta=25°C Unless otherwise specified)

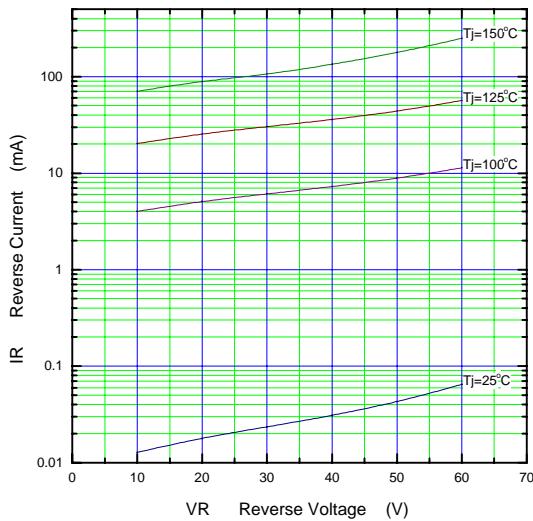
Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V _{FM}	I _{FM} =25A	0.58	V
Reverse current	I _{RRM}	V _R =V _{RRM}	50	mA
Thermal resistance	R _{th(j-c)}	Junction to case	0.75	°C/W

■ Characteristics

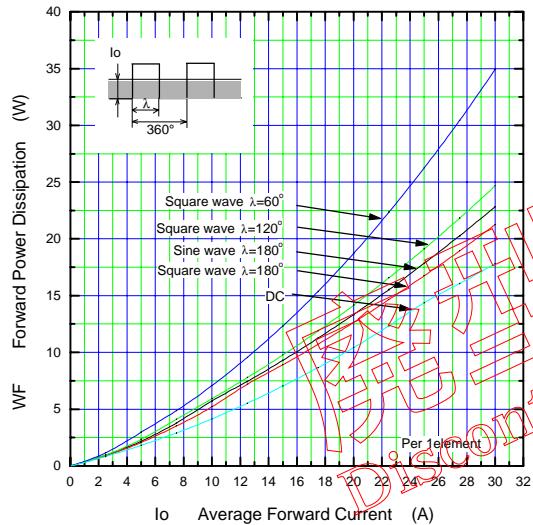
Forward Characteristic (typ.)



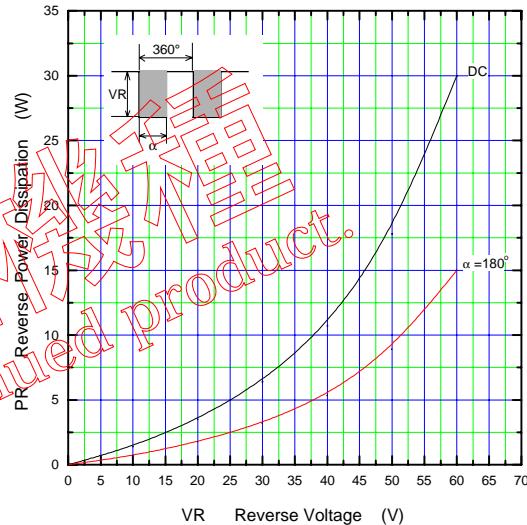
Reverse Characteristic (typ.)



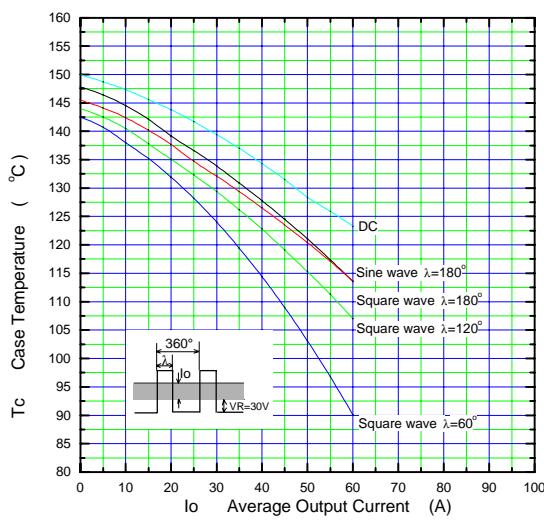
Forward Power Dissipation



Reverse Power Dissipation



Current Derating (Io-Tc)



λ : Conduction angle of forward current for each rectifier element
Io: Output current of center-tap full wave connection

Junction Capacitance Characteristic (typ.)

